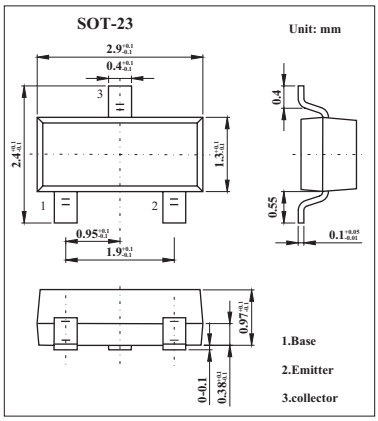
Silicon NPN Epitaxial

2SC3121



■ Features

- High Transition Frequency :fT=1500MHz (Typ.)
- Exellent Linearity

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	15	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	25	mA
Base current	I_B	50	mA
Collector Power Dissipation	P_C	150	mW
Junction temperature	T_j	125	℃
Storage temperature Range	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 15V, I_E = 0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 3V, I_C = 0			1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	15			V
DC current gain	h_{FE}	V_{CE} = 3 V, I_C = 8 mA	60	150	320	
Transition Frequency	f_T	V_{CE} = 10 V, I_C = 8mA	1100	1500		MHz
Conversion Output Capacitance	C_{ob}	V_{CB}=10V,I_E=0mA,f=1MHZ		0.9	1.3	pF
Collector-Bace Time Constant	$C_{c.rbb2}$	V_{CB}=10V,I_C=8mA,f=30MHZ		7	12	ps

■ Marking

Marking	HC